

Low Resistance Ohmic contact on epitaxial MOVPE grown β -Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ films

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Abstract— We report on the realization of record low resistance Ohmic contacts to MOVPE-grown heavily Si-doped β -Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ epitaxial films. Transfer length measurement (TLM) patterns were fabricated on the heavily Si-doped homoepitaxial β -Ga₂O₃ films with electron concentration (n) ranging from 1.77 to 3.23×10^{20} cm⁻³. Record low specific contact resistance (ρ_c) and total contact resistance (R_c) of 1.62×10^{-7} Ω .cm² and 0.023 Ω .mm were realized for β -Ga₂O₃: Si films with $n > 3 \times 10^{20}$ cm⁻³. TLM structures were also fabricated on heavily Si doped coherently strained β -(Al_xGa_{1-x})₂O₃/ β -Ga₂O₃ ($x=12\%$, 17% and 22%) films. The film with 12% Al composition ($n=1.23 \times 10^{20}$ cm⁻³) showed ρ_c of 5.85×10^{-6} Ω .cm², but it increased to 2.19×10^{-4} Ω .cm² for a layer with a 22% Al composition. Annealing the samples post metal deposition has generally led to a decrease in contact resistance, but for high Al content β -(Al_x, Ga_{1-x})₂O₃, the contact resistance did not change significantly after the annealing process. The low contact resistance values measured in this work are very promising for the fabrication of high frequency power devices.

Index Terms—Ga₂O₃, (Al_xGa_{1-x})₂O₃, MOVPE, specific contact resistance, heavy doping, TLM, Hall.

I. INTRODUCTION

Beta gallium oxide (β -Ga₂O₃) has received significant attention in semiconductor research for applications in power electronic devices due to its fundamental properties, including a high breakdown field of ~ 8 MV/cm[1], availability of high quality melt grown native substrates [2], and controllable donor doping [3, 4]. The availability of high quality Ga₂O₃ substrates has resulted in the rapid development of high quality β -Ga₂O₃ epilayers and devices [5-8]. Excellent device results, such as breakdown voltages and critical fields exceeding 2.5 kV and 3 MV/cm, have been reported on numerous lateral and vertical β -Ga₂O₃ power devices [6, 9-12]. However, as a gateway to the external world, reliable low resistance Ohmic contacts are critical for the efficient performance of any device. High contact resistance at the metal/ β -Ga₂O₃ junction leads to slower device switching speeds and device failure due to local contact heating from a significant voltage drop at the junction during device operation[13, 14].

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Various techniques, including ion implantation [15], spin-on-glass [16], and regrowth methods [5, 17], have been employed to reduce contact resistance at the source/drain (S/D) ohmic contacts in Ga₂O₃ MOSFETs and MESFETs. Both ion implantation and spin-on-glass methods expose the material to a high annealing temperature (~ 900 - 1200 °C) and potentially deteriorate the quality of the device's active region [15, 16]. However, regrowth process is typically performed at a much lower substrate temperature (~ 600 °C) and a low contact resistance can be achieved without affecting the material quality. Recently, MOVPE based regrowth process has been applied to fabrication of various FETs, realizing a metal/n⁺-Ga₂O₃ contact resistance as low as 0.08 Ω .mm and ρ_c of $\sim 8 \times 10^{-7}$ Ω .cm² [5]. However, a systematic study to heavily dope β -Ga₂O₃ epitaxial layers using MOVPE and achieve low contact resistance is still lacking. In this work, we report on the demonstration of record low resistance Ohmic contacts on heavily Si doped epitaxial β -Ga₂O₃ and pseudomorphic Si doped β -(Al_xGa_{1-x})₂O₃ epilayers with varying Al composition.

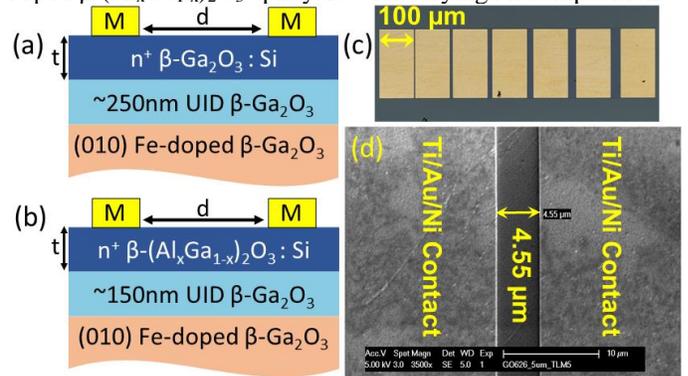


Fig. 1. Schematic cross-sectional view of the heavily Si doped (a) β -Ga₂O₃ and (b) β -(Al_xGa_{1-x})₂O₃/ β -Ga₂O₃ heterostructure with Ti/Au/Ni metal stack for Ohmic contact. (c) Optical microscope image showing the TLM pattern (d) SEM image verifying the gap spacing, d .

II. MATERIALS GROWTH AND DEVICE FABRICATION

Three heavily Si doped homoepitaxial β -Ga₂O₃ films (samples A, B, and C, see Table I) and three fully strained heavily Si doped β -(Al_xGa_{1-x})₂O₃/ β -Ga₂O₃ heterostructures with Al composition (x) of 12% (Sample D), 17% (sample E), and 22% (sample F) were grown using Agnitron Technology's Agilis 100 MOVPE reactor on (010) β -Ga₂O₃:Fe substrates. The doped β -Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ layers were grown at ~ 600 °C on an ~ 250 nm and ~ 150 nm thick unintentionally doped (UID) Ga₂O₃ buffer layers (Fig. 1), respectively, with TEGa, TEAl, O₂, and silane (SiH₄) as precursors, and Ar as carrier gas. The layer thickness and doping concentration for the heavily Si doped β -Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ films are shown in Table I. The purity of the phase, Al composition (x), and layer thickness for the β -(Al_xGa_{1-x})₂O₃ layers were determined using HRXRD [18]. Hall effect measurements were

performed on each of the samples to determine their electron concentration (n), mobility (μ_e), and sheet resistance (R_{sh}) as presented in Table I. The films were then processed into linear transmission line model (TLM) test structures to characterize their contact resistance. TLM structures were mesa isolated to the β -Ga₂O₃ substrate using BCl₃ chemistry-based reactive ion etching (RIE) process. A 20 nm/150 nm/50 nm Ti/Au/Ni metal stack was deposited via e-beam evaporation and was annealed at 470 °C in N₂ for 1min. Four probe current – voltage (I-V) measurements were performed on the TLM structures to obtain the specific contact resistance (ρ_c) of the ohmic contact.

III. RESULTS AND DISCUSSIONS

The TLM measurements were performed at room temperature before and after rapid annealing of the contacts. Fig. 2(a) and 2(b) show the total resistance between electrodes as a function of electrode spacing, d , for representative β -Ga₂O₃ epilayer (sample C, $n = 3.23 \times 10^{20} \text{ cm}^{-3}$) and β -(Al_{0.12}Ga_{0.88})₂O₃/ β -Ga₂O₃ heterostructure (sample D, $n = 1.23 \times 10^{20} \text{ cm}^{-3}$) samples after contact annealing. The output resistance has shown strong linear dependence on electrode spacing for all the samples, and the TLM data was fitted to extract sheet resistance (R_{sh}), specific contact resistance (ρ_c), total contact resistance (R_c), and transfer length (L_T) for the respective samples. For the β -Ga₂O₃ and β -(Al_{0.12}Ga_{0.88})₂O₃ layers ρ_c of $\sim 10^{-7} \Omega \cdot \text{cm}^2$ and $\sim 6 \times 10^{-6} \Omega \cdot \text{cm}^2$, respectively, were obtained.

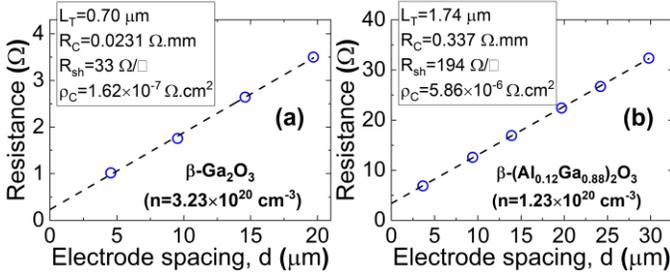


Fig. 2. Total resistance between electrodes versus electrode spacing for heavily Si doped MOVPE grown: (a) β -Ga₂O₃ ($n = 3.23 \times 10^{20} \text{ cm}^{-3}$) and (b) β -(Al_{0.12}Ga_{0.88})₂O₃ ($n = 1.23 \times 10^{20} \text{ cm}^{-3}$) measured after metallization contact anneal. The circular symbols are measured data and the broken lines are linear fitting to extract R_{sh} , R_c , ρ_c and L_T parameters.

Table I. Electron concentration (n), Hall electron mobility (μ_e), and sheet resistance ($R_{sh-Hall}$) of the Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ layers measured by Hall effect measurements. The layers thickness (t) and sheet resistance measured by TLM method (R_{sh-TLM}) is also presented.

Samples	t (nm)	n (cm ⁻³)	μ_e (cm ² V ⁻¹ s ⁻¹)	$R_{sh-Hall}$ (Ω/□)	R_{sh-TLM} (Ω/□)
A	145	1.77×10^{20}	25.2	97	107
B	65	2.51×10^{20}	53.1	72	87
C	170	3.23×10^{20}	38.2	30	33
D	75	1.23×10^{20}	31.1	216	194
E	110	1.22×10^{20}	16.2	284	290
F	84	5.49×10^{19}	24.9	608	514

The sheet resistance (R_{sh}) extracted from the TLM after contact annealing is compared with the values measured from Hall effect measurements (Table I). The R_{sh} values obtained from the two methods are very comparable, showing the consistency of the results obtained for each film. Fig 3. shows

the specific contact resistance (ρ_c) and total contact resistance (R_c) measured post contact annealing as a function of electron concentration for Ga₂O₃:Si. Both ρ_c and R_c decreased with the increase in doping concentration. All the Ga₂O₃ epitaxial layers studied in this work ($n > 1.7 \times 10^{20} \text{ cm}^{-3}$) demonstrated ρ_c of $< 1.66 \times 10^{-6} \Omega \cdot \text{cm}^2$ (the lowest being $1.62 \times 10^{-7} \Omega \cdot \text{cm}^2$), much lower than all the specific contact resistance values reported in the literature so far [5, 15, 19-21]. The lowest specific contact resistance (ρ_c) of $1.62 \times 10^{-7} \Omega \cdot \text{cm}^2$ obtained in this work is lower than the best specific constant resistance reported by the MOVPE regrowth method by $\sim 4 \times$ ref. [5] and ion implantation method by $23 \times$ ref. [15]. The R_c values were also lower than $0.05 \Omega \cdot \text{mm}$ for Ga₂O₃ samples with $n > 2.5 \times 10^{20} \text{ cm}^{-3}$. Both ρ_c and R_c values obtained in this work are the lowest among UWBG materials, suggesting that MOVPE- regrown contacts could play a significant role in the future development of efficient and fast switching RF devices.

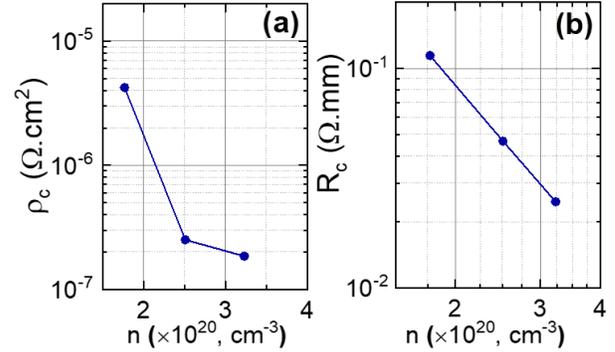


Fig. 3. (a) ρ_c and (b) R_c as a function of carrier concentration for heavily Si doped β -Ga₂O₃ measured after metallization contact anneal.

Fig. 4(a) and 4(b) presents the specific contact resistance (ρ_c) and total contact resistance (R_c) measured post contact annealing as a function of Al composition for β -(Al_xGa_{1-x})₂O₃/ β -Ga₂O₃ heterostructures. The left panel (y-axis) for both figures show the measured electron concentration (n). The plots also include the ρ_c , R_c , and n for pure Ga₂O₃ to indicate β -(Al_xGa_{1-x})₂O₃ with $x=0$. With the increase in the Al composition of the β -(Al_xGa_{1-x})₂O₃ from 0 to 22%, the n decreased, and the ρ_c and R_c increased. When the Al composition in the β -(Al_xGa_{1-x})₂O₃ increased from 0 (i.e., pure Ga₂O₃) to 12% (i.e., β -(Al_{0.12}Ga_{0.88})₂O₃) the ρ_c increased by more than an order of magnitude (from 1.62×10^{-7} to $5.86 \times 10^{-6} \Omega \cdot \text{cm}^2$) but was still comparable to the best ρ_c reported for Si implanted Ga₂O₃ [15]. For the β -(Al_xGa_{1-x})₂O₃ with Al composition of 22%, the specific contact resistance obtained was $2.19 \times 10^{-4} \Omega \cdot \text{cm}^2$. Similarly, the total contact resistance increased with the increase in Al composition.

It is a common practice to perform rapid thermal annealing following metallization at a temperature ranging from 400 to 500 °C to improve the contact resistance at the metal/ n^+ -Ga₂O₃ junction [15, 19, 22]. In this work, as indicated above, we measured the contact resistance of each of the samples before and after annealing the Ti/Au/Ni metal stack contacts in N₂ at 470 °C to study the effect annealing on the β -(Al_xGa_{1-x})₂O₃ layers. Table II compares the ρ_c for the Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ samples. For the Ga₂O₃ films, the ρ_c decreased following the annealing process, showing the expected improvement in contact resistance. But, for β -(Al_xGa_{1-x})₂O₃ layers, a significant

decrease in ρ_c after annealing was observed only for a film with lower Al composition (12%). For higher Al composition β -(Al_xGa_{1-x})₂O₃, the ρ_c stayed relatively the same or increased following the annealing process (See Table II). This is likely due to the differences in interfacial reaction and interface chemical composition of Ti/AlGaO as compared to Ti/Ga₂O₃ annealed interfaces[14].

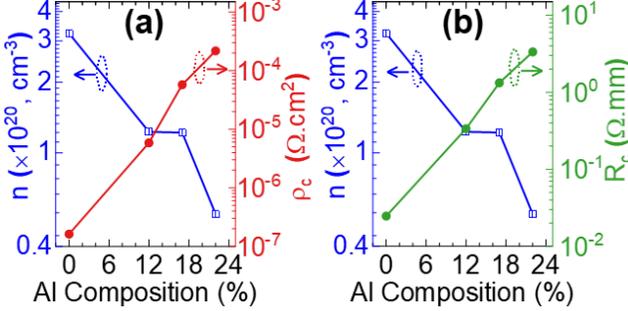


Fig. 4. (a) ρ_c and (b) R_c as a function of Al composition measured after metallization contact anneal. The left panel on both figures shows electron concentration (n) dependence on Al composition. The values at $x=0$ is for pure Ga₂O₃.

Table II. Compares ρ_c values measured before and after contact annealing. R_c measured after the contact annealing is shown.

Samples	ρ_c ($\Omega \cdot \text{cm}^2$)		R_c ($\Omega \cdot \text{mm}$)
	[Pre-anneal]	[Post-anneal]	[Post-anneal]
A	4.23×10^{-6}	1.66×10^{-6}	0.110
B	1.68×10^{-6}	2.51×10^{-7}	0.047
C	1.12×10^{-6}	1.62×10^{-7}	0.023
D	1.30×10^{-5}	5.86×10^{-6}	0.340
E	3.56×10^{-5}	5.77×10^{-5}	1.270
F	3.96×10^{-4}	2.19×10^{-4}	3.350

A heavily Ge doped MOVPE grown β -Ga₂O₃ film (GeH₄/N₂ as Ge source) with $n=2.6 \times 10^{20} \text{ cm}^{-3}$ and $\mu_c \sim 38 \text{ cm}^2/\text{Vs}$ [18, 23] was also fabricated into TLM and ρ_c and R_c values of $2.1 \times 10^{-6} (\Omega \cdot \text{cm}^2)$ and $0.06 (\Omega \cdot \text{mm})$ were obtained. Although less desirable as a dopant for Ga₂O₃ due to its strong process dependence and severe memory effect, Ge can still be used to obtain low resistance Ohmic contacts for FETs [6, 10, 23].

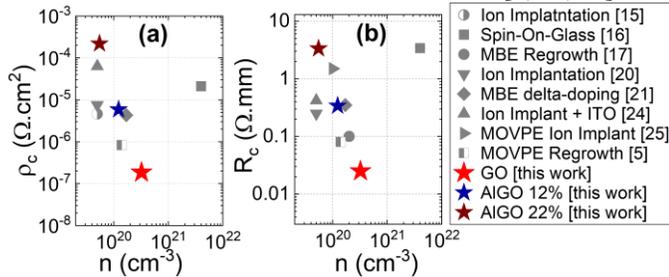


Fig. 5. ρ_c (a) and R_c (b) from this work as compared to the best reported results from various methods [5, 15-17, 20, 21, 24, 25]. Results measured for β -(Al_xGa_{1-x})₂O₃ films with Al composition of 12% and 22% are also included.

Fig. 5(a) and 5(b) benchmarks our specific contact resistance (ρ_c) and total contact resistance (R_c) values with the existing literature reports. The comparison shows that the obtained ρ_c and R_c values for the Ga₂O₃ is the lowest of all the values reported. Even for β -(Al_{0.12}Ga_{0.88})₂O₃, the obtained ρ_c and R_c values are comparable to those reported for pure Ga₂O₃ using ion implantation method [20]. Thus, utilizing low temperature MOVPE epitaxy, heavily doped Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃

epitaxial films can be grown to realize a low metal/semiconductor contact resistance. Such a result is very encouraging for high frequency devices where low parasitic resistance is critical.

IV. CONCLUSION

We successfully demonstrated record low resistance Ohmic contacts to MOVPE-grown heavily Si doped β -Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ epitaxial films. For β -Ga₂O₃: Si with an electron concentration of $3.23 \times 10^{20} \text{ cm}^{-3}$, ρ_c and R_c values of $1.62 \times 10^{-7} \Omega \cdot \text{cm}^2$ and $0.023 \Omega \cdot \text{mm}$ were obtained. For β -(Al_xGa_{1-x})₂O₃, the electron concentration was found to decrease with the increase in Al composition, and thus led to an increase in ρ_c and R_c . The record low metal/semiconductor contact resistance measured both for β -Ga₂O₃ and β -(Al_xGa_{1-x})₂O₃ in this work will have significant impact in advancing the performance of RF devices, where low parasitic resistances is paramount.

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